

Amendments to the Specification

Please amend the title as follows:

Methods for Forming Wordlines, Transistor Gates, and Conductive Interconnects, ~~and~~
~~Wordline, Transistor Gate, and Conductive Interconnect Structures~~

Please amend the paragraph on page 5 lines 20-21 of the specification as follows:

Fig. 1 illustrates a semiconductor wafer fragment at a preliminary step of a prior art method for forming a wordline.

Please amend the paragraph on page 6 lines 1-2 of the specification as follows:

Fig. 3 illustrates a semiconductor wafer fragment at a preliminary step of a prior art method for forming PROM device.

Please amend the paragraph on page 6 lines 5-7 of the specification as follows:

Fig. 5 illustrates a semiconductor wafer fragment at a preliminary step of a first embodiment method of the present invention for forming a wordline.